The 1N432 is a hermetically sealed silicon junction diode designed for general purpose applications and providing extreme stability, wide temperature range, high back resistance (100 megohms or more), and high ratio of back to forward resistance. The flexible terminal leads may be soldered or welded directly to the terminals of circuit components without the use of sockets. Standard inline subminiature sockets may be used by cutting the leads to a suitable length.

MECHANICAL DATA

CASE: Metal and Glass
BASE: None (0.016" tinned d wet wire. Length: 1.0" min.
Spacing: 0.080" center-to-center)
TERMINAL CONNECTIONS: (Black Dot is adjacent to Cathode Terminal)
MOUNTING POSITION: Any

ELECTRICAL DATA

RATINGS - ABSOLUTE MAXIMUM VALUES: (at 25°C)
- Peak Inverse Voltage: 40 volts
- Continuous Inverse Voltage: 35 volts
- Average Rectified Current: 60 ma.
- Average Rectified Current (100°C): 40 ma.
- Peak Rectified Current: 120 ma.
- Surge Current (for 1 sec.): 400 ma.
- Ambient Temperature Range: -55 to +150°C
- Dissipation at:
  - 25°C: 150 mw.
  - 65°C: 110 mw.
  - 100°C: 75 mw.
  - 150°C: 25 mw.

CHARACTERISTICS:
- Maximum Inverse Current at +10 volts: 0.05 ma.
- Minimum Forward Current at +1.0 volt: 10.0 ma.
TYPICAL TEMPERATURE CHARACTERISTICS

Reverse Voltage - Volts

<table>
<thead>
<tr>
<th>70</th>
<th>60</th>
<th>50</th>
<th>40</th>
<th>30</th>
<th>20</th>
<th>10</th>
</tr>
</thead>
<tbody>
<tr>
<td>100°C</td>
<td>25°C</td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
</tbody>
</table>

Forward Current - mA

<table>
<thead>
<tr>
<th>60</th>
<th>40</th>
<th>20</th>
<th>10</th>
</tr>
</thead>
<tbody>
<tr>
<td>1.0</td>
<td></td>
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</tbody>
</table>

Forward Voltage Volts

<table>
<thead>
<tr>
<th>2</th>
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Reverse Current - µA

<table>
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<tr>
<th>4</th>
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</thead>
</table>

SILICON JUNCTION DIODE

RAYTHEON MANUFACTURING COMPANY

RECEIVING AND CATHODE RAY TUBE OPERATIONS

July 29, 1955

NEWTON 58, MASS.